

ABSTRACT OF THE DISCLOSURE

A semiconductor device equipped with information storage capacitor comprising a first capacitor electrode, an oxide film, a second capacitor electrode and insulating films containing silicon as a main constituting element, wherein at least one of first and second capacitor electrodes contains as a main constituting element at least one element selected from rhodium, ruthenium, iridium, osmium and platinum, and as an adding element at least one element selected from palladium, nickel, cobalt and titanium, is excellent in adhesiveness between the capacitor electrodes and the insulating films.